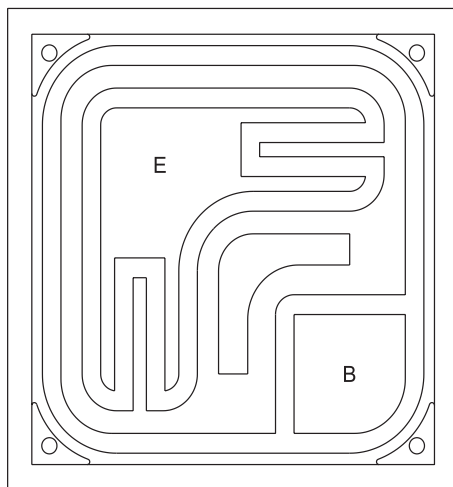


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	20 x 20 MILS
Die Thickness	8.0 MILS
Base Bonding Pad Area	4.9 x 4.9 MILS
Emitter Bonding Pad Area	6.4 x 6.4 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 16,000Å

GEOMETRY**BACKSIDE COLLECTOR** R1**GROSS DIE PER 4 INCH WAFER**

28,250

PRINCIPAL DEVICE TYPES

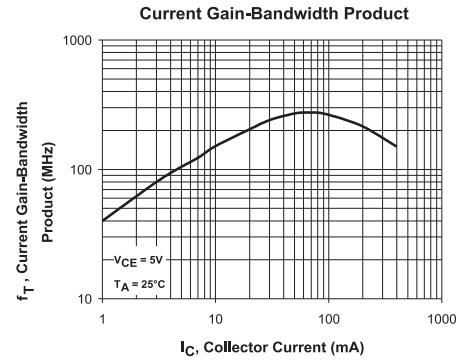
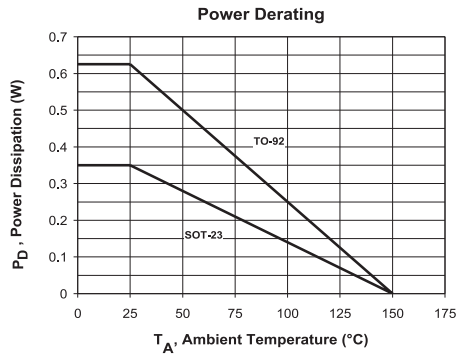
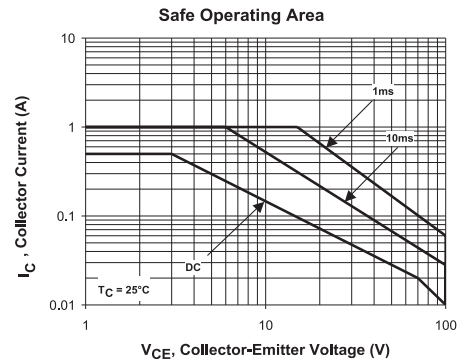
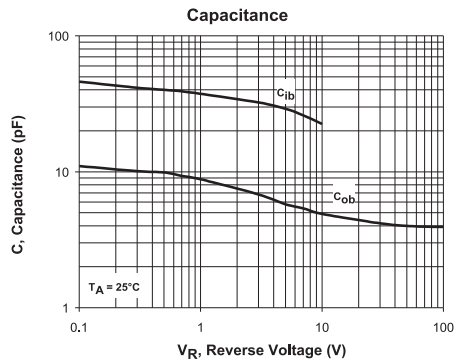
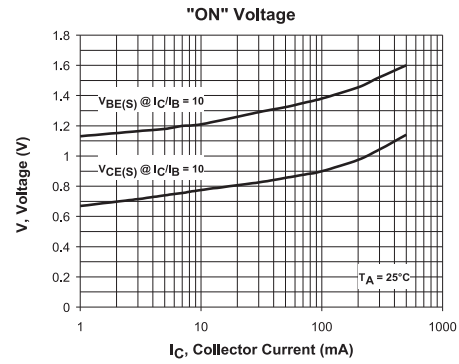
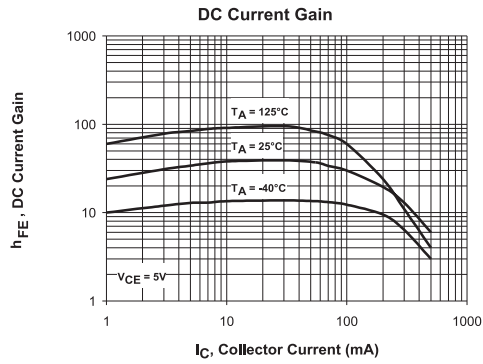
MPSA28

MPSA29

CMPTA29

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R3 (21-September 2003)



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